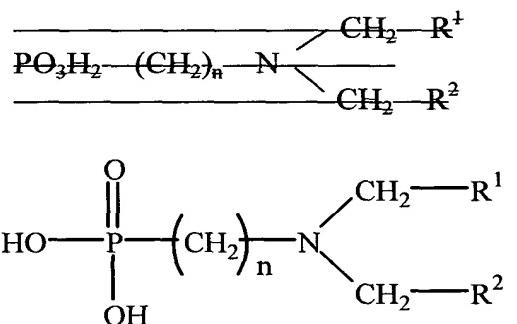


CLAIM AMENDMENTS

1. (Currently Amended) A chemical-mechanical polishing system for a substrate comprising:

- (a) a liquid carrier,
- (b) a polishing pad and/or an abrasive,
- (c) a per-type oxidizer, and
- (d) an additive of the formula



wherein R¹ is a phosphono group or a carboxyl group, R² is a phosphono group or a carboxyl group, and n is an integer from 1 to 50.

2. (Canceled).

3. (Currently Amended) The chemical-mechanical polishing system of claim 1, wherein R¹ and R² are is a carboxyl groups group.

4. (Original) The chemical-mechanical polishing system of claim 1, wherein both a polishing pad and an abrasive are present, and the abrasive is fixed on the polishing pad.

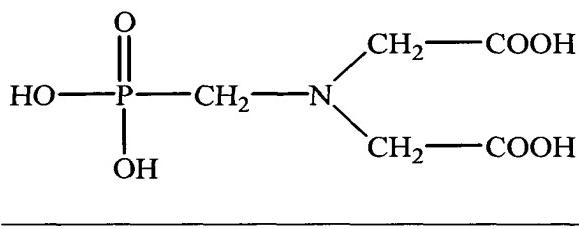
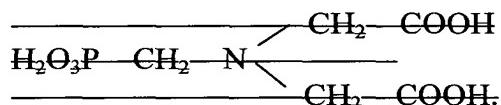
5. (Original) The chemical-mechanical polishing system of claim 1, wherein an abrasive is present in particulate form and is suspended in the carrier.

6. (Original) The chemical-mechanical polishing system of claim 5, wherein the abrasive is a metal oxide.

7. (Original) The chemical-mechanical polishing system of claim 6, wherein the abrasive is silica.

8. (Original) The chemical-mechanical polishing system of claim 1, wherein the carrier is water.

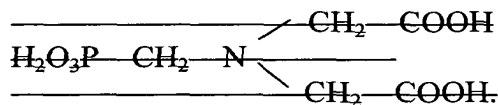
9. (Currently Amended) The chemical-mechanical polishing system of claim 3, wherein the additive is

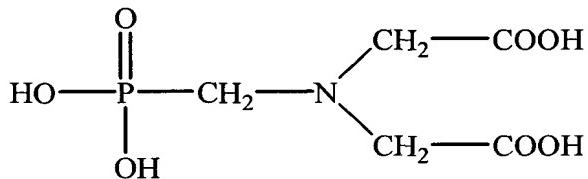


or the salt thereof.

10. (Original) The chemical-mechanical polishing system of claim 1, wherein the per-type oxidizer is hydrogen peroxide.

11. (Currently Amended) The chemical-mechanical polishing system of claim 1, wherein the carrier is water, both a polishing pad and an abrasive are present, the abrasive is a metal oxide, the per-type oxidizer is hydrogen peroxide, and the additive is





or the salt thereof.

12-24. (Canceled).

25. (New) The chemical-mechanical polishing system of claim 9, wherein both a polishing pad and an abrasive are present, and the abrasive is fixed on the polishing pad.

26. (New) The chemical-mechanical polishing system of claim 9, wherein an abrasive is present in particulate form and is suspended in the carrier.

27. (New) The chemical-mechanical polishing system of claim 26, wherein the abrasive is a metal oxide.

28. (New) The chemical-mechanical polishing system of claim 27, wherein the abrasive is silica.

29. (New) The chemical-mechanical polishing system of claim 28, wherein the carrier is water.

30. (New) The chemical-mechanical polishing system of claim 29, wherein the per-type oxidizer is hydrogen peroxide.

31. (New) The chemical-mehcanical polishing system of claim 11, wherein the abrasive is fixed on the polishing pad.

32. (New) The chemical-mechanical polishing system of claim 11, wherein the abrasive is present in particulate form and is suspended in the carrier.

33. (New) The chemical-mechanical polishing system of claim 32, wherein the abrasive is silica.